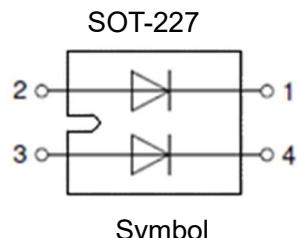


JU100K2

Description

- 1) Low forward voltage drop
- 2) Two fully independent diodes
- 3) Fully insulated package
- 4) Easy to use and parallel
- 5) Industry standard outline
- 6) Designed and qualified for industrial level



Typical Application

Optimized for power conversion: welding and industrial SMPS applications

Absolute Maximum Ratings (Packaged into SOT-227, unless otherwise specified, $T_{CASE}=25^{\circ}\text{C}$)

Parameter	Test Conditions	Symbol	Values	Unit
Junction temperature range		T_j	-40-150	°C
Storage temperature range		T_{stg}	-40-150	°C
Repetitive peak reverse voltage	$T_j=25^{\circ}\text{C}$	V_{RRM}	500	V
Non-repetitive peak reverse voltage	$T_j=25^{\circ}\text{C}$	V_{RSM}	600	V
Average forward current	$T_C=115^{\circ}\text{C}$	$I_{F(AV)}$	100	A
Peak on-state surge current	$t_P=10\text{ms}, \sin 180^{\circ}, T_j=25^{\circ}\text{C}$	I_{FSM}	1000	A
I^2t value	$t_P=10\text{ms}, \sin 180^{\circ}, T_j=25^{\circ}\text{C}$	I^2t	5000	A^2s
Max reverse recovery current	$I_F=50\text{A}; V_R=400\text{V}, -di/dt=200\text{A}/\mu\text{s}, T_j=25^{\circ}\text{C}$	I_{RM}	10	A
	$I_F=50\text{A}; V_R=400\text{V}, di/dt=200\text{A}/\mu\text{s}, T_j=125^{\circ}\text{C}$		18	
Reverse recovery time	$I_F=1\text{A}; V_R=30\text{V}, -di/dt=100\text{A}/\mu\text{s}, T_j=25^{\circ}\text{C}$	t_{rr}	42	ns
	$I_F=50\text{A}; V_R=400\text{V}, -di/dt=200\text{A}/\mu\text{s}, T_j=25^{\circ}\text{C}$		75	
	$I_F=50\text{A}; V_R=400\text{V}, -di/dt=200\text{A}/\mu\text{s}, T_j=125^{\circ}\text{C}$		120	
Recovered charge	$I_F=50\text{A}; V_R=400\text{V}, -di/dt=200\text{A}/\mu\text{s}, T_j=25^{\circ}\text{C}$	Q_{rr}	400	nC
	$I_F=50\text{A}; V_R=400\text{V}, -di/dt=200\text{A}/\mu\text{s}, T_j=125^{\circ}\text{C}$		1100	
Isolation voltage	A.C 50Hz(1s/1min)	V_{iso}	3000/2500	V



Rectifier Diode Module

Electrical Characteristics(Packaged into SOT-227, unless otherwise specified, $T_{CASE}=25^{\circ}\text{C}$)

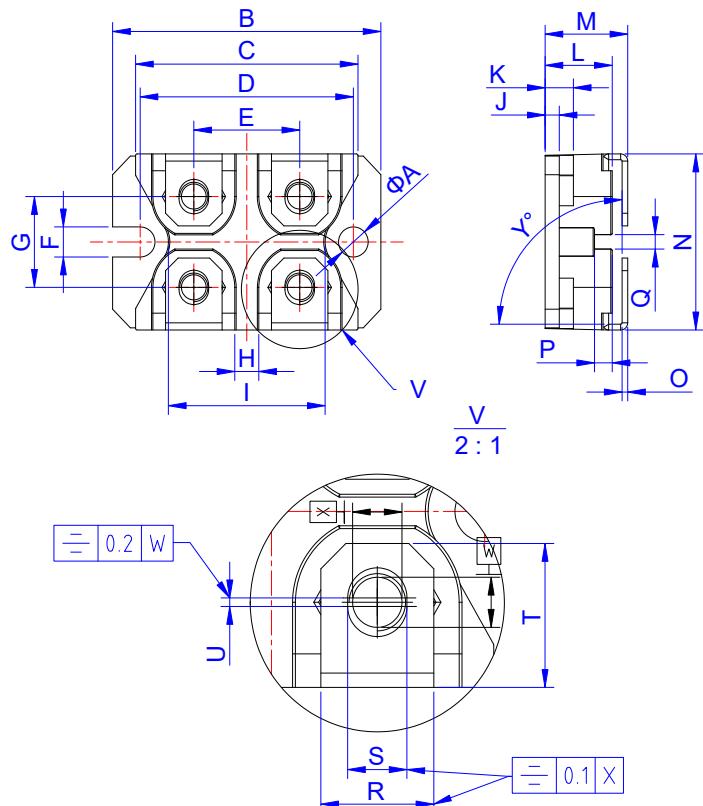
Parameter	Test Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	$I_F=100\text{A}, T_j=25^{\circ}\text{C}$	V_F	-	-	1.8	V
Reverse leakage current	$V_R=V_{RRM}, T_j=25^{\circ}\text{C}$	I_R	-	-	0.01	mA
	$V_R=V_{RRM}, T_j=150^{\circ}\text{C}$		-	-	1	mA

Thermal Characteristics(Packaged into SOT-227, unless otherwise specified, $T_{CASE}=25^{\circ}\text{C}$)

Parameter	Test Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Junction to case(per diode)		$R_{th(j-c)}$	-	-	0.5	°C/W
Case to heatsink		$R_{th(c-s)}$	-	0.125	-	
Weight			-	30	-	g
Mounting torque	Base plate to heatsink screw M4	M	1.0	-	1.5	N·m
	Electrode to terminal screw M4		1.0	-	1.5	N·m
Case style			SOT-227			

Ordering Information

<u>J</u>	<u>U</u>	<u>100</u>	<u>K2</u>	<u>-06</u>
<u>JieJie Semiconductor Co.,Ltd</u>				<u>06: $V_{RSM} \geq 600\text{V}$</u>
<u>General purpose rectifier diode</u>		<u>$I_{F(AV)}=100\text{A}$</u>		<u>Dual circuit module</u>

Mechanical Characteristics


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.1	4.2	4.4	0.161	0.165	0.173
B	38.0	38.2	38.4	1.496	1.504	1.512
C	31.1	31.5	31.9	1.224	1.240	1.256
D	30.1	30.2	30.3	1.185	1.189	1.193
E	14.8	15.0	15.2	0.583	0.591	0.598
F	4.1	4.2	4.4	0.161	0.165	0.173
G	12.3	12.5	12.7	0.484	0.492	0.500
H		4.2			0.165	
I		21.6			0.850	
J		2			0.079	
K		4.05			0.159	
L		9.5			0.374	
M	11.6	11.9	12.2	0.457	0.469	0.480
N	24.7	25.1	25.5	0.972	0.988	1.004
O		0.8			0.031	
P		2.6			0.102	
Q		1.7			0.067	
R		8			0.315	
S	4.1	4.2	4.4	0.161	0.165	0.173
T		10.7			0.421	
U		1			0.039	
Y	89°	90°	91°	89°	90°	91°

Technical requirements:

1. Unmarked tolerances of dimension are performed in accordance with GB/T 1804-2000 Level C
2. Unmarked tolerances of form and position are performed in accordance with GB/T 1184-1996 Level L

Package Information-SOT-227

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	8	80	800

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